SLDS034 - DECEMBER 1986 - REVISED JULY 1889

- Each Device Drives 32 Lines
- 180-V Open-Drain Parallel Outputs
- 220-mA Parallel Output Sink Current Capability
- CMOS-Compatible Inputs
- Strobe Input Provided
- Serial Data Output for Cascade Operation
- Inputs Have Built-In Electrostatic Discharge Protection

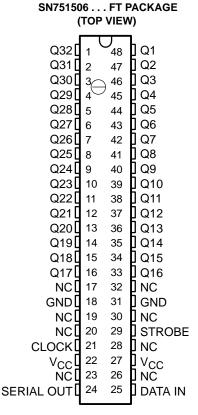
description

The SN751506 and the SN751516 are monolithic integrated circuits designed to drive the scan lines of a dc plasma panel display. The SN751516 pin sequence is reversed from the SN751506 for ease in printed-circuit-board layout.

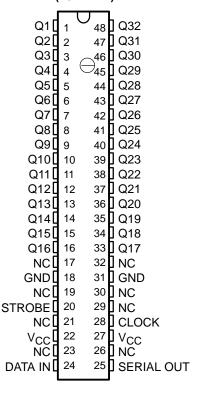
Each device consists of a 32-bit shift register and 32 OR gates. Serial data is entered into the shift register on the high-to-low transition of the clock input. When STROBE is low, all Q outputs are in the off state. Outputs are open-drain JFET transistors with a breakdown voltage in excess of 180 V. The outputs have a 220-mA sink current capability in the on state. Only one Q output should be allowed to be in the on state at a time.

SERIAL OUT from the shift register can be used to cascade shift registers. This output is not affected by the STROBE input. All inputs are CMOS compatible with ESD protection built in.

The SN751506 and SN751516 are characterized for operation from 0°C to 70°C.



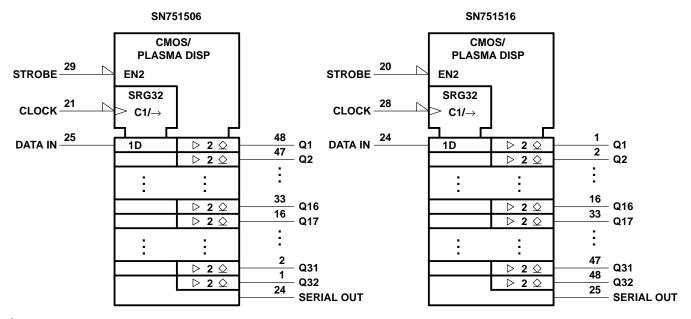
SN751516...FT PACKAGE (TOP VIEW)



NC - No internal connection

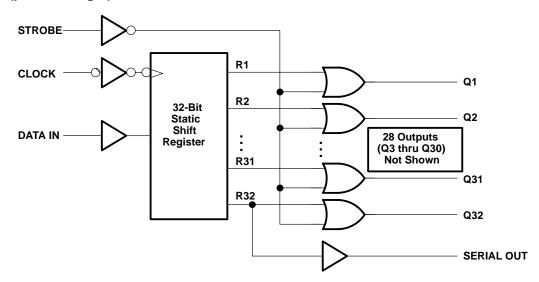


logic symbols†



[†] These symbols are in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



FUNCTION TABLE

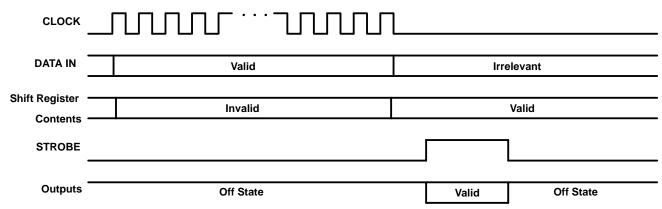
FUNCTION	CONTROL INPUTS		SHIFT REGISTERS	OUTPUTS			
FUNCTION	CLOCK	STROBE	R1 THRU R32	SERIAL	QI THRU Q32		
Load	↓ No ↓	X X	Load and shift [‡] No change	R32 R32	Determined by STROBE		
Strobe	X X	L H	As determined above	R32 R32	All high impedance R1 through R32		

H = high level, L = low level, X = irrelevant, \downarrow = high-to-low transition.

[‡]R32 takes on the state of R31, R31 takes on the state of R30, . . . R2 takes on the state of R1, and R1 takes on the state of the data input.

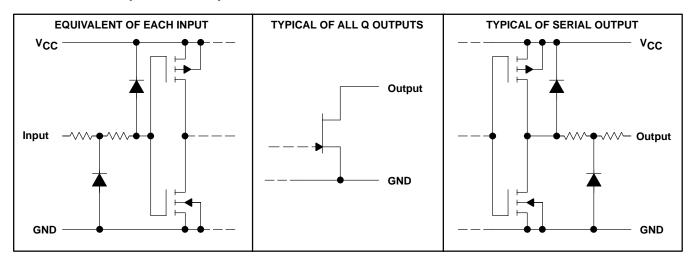


typical operating sequence



[†]Only 1 bit in 32 should be low in the input data.

schematics of inputs and outputs



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Supply voltage range, V _{CC} (see Note 1) –0.4 V to 7 V
On-state Q output voltage range, VO –0.4 V to 125 V
Off-state Q output voltage range, VO0.4 V to 180 V
Input voltage range, V _I –0.4 V to V _{CC} + 0.4 V
Serial output voltage range
Q output on-state time duration (see Note 2)
Q output duty cycle (see Note 2)
Continuous total power dissipation at (or below) 25°C free-air temperature (see Note 3) 1025 mW
Operating free-air temperature range, T _A 0°C to 70°C
Storage temperature range–55°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds

NOTES: 1. Voltage values are with respect to GND.

- 2. Only one Q output should be on at a time.
- 3. For operation above 25°C free-air temperature, derate linearly to 656 mW at 70°C at the rate of 8.2 mW/°C.



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recommended operating conditions

			MIN	NOM	MAX	UNIT
Supply voltage, V _{CC}		4	5	6	V	
Peak on-state Q output voltage, VO(on)			-	110	V	
High-level input voltage, V _{IH}	V _{CC} = 4 V		3.2			٧
	VCC = 6 V		4.8			V
Lauria de la	$V_{CC} = 4 V$				0.8	V
Low-level input voltage, V _{IL}	V _{CC} = 6 V				1.2	V
Output current, I _O (T _A = 25°C)				220	mA	
Clock frequency, f _{clock}				200	kHz	
Pulse duration, CLOCK high or low, tw(CLK)		1.5†			μs	
Pulse duration, DATA, t _{wD}		5			μs	
Pulse duration, STROBE, t _W (STRB)			2			μs
Setup time, DATA IN before CLOCK ↓, t _{SU}		1			μs	
Hold time, DATA IN after CLOCK↓, t _h		1.2			μs	
Operating free-air temperature, T _A		0		70	°C	

[†] The minimum clock period is 5 μs.

electrical characteristics, V_{CC} = 5 V, T_A = 25°C

PARAMETER			TEST CONDITIONS	MIN	TYP	MAX	UNIT	
Vон	High-level output voltage	SERIAL OUT		$I_{OH} = -0.1 \text{ mA}$	4.5			V
VOL	Low-level output voltage	Q outputs		I _{OL} = 180 mA		6	10	٧
		SERIAL OUT		I _{OL} = 0.1 mA			0.5	
IO(off)	Off-state output current	Q outputs		V _{OH} = 110 V		-	1	μА
loL	Low-level output current	Q outputs		V _{OL} = 16 V	220			mA
lн	IH High-level input current		$V_I = V_{CC}$			1	μΑ	
Ι _Ι L	Low-level input current		V _I = 0			-1	μΑ	
Ci	Input capacitance						15	pF
lcc	Complex accompant			All Q outputs off			1	A
	Supply current		One Q output on		20	40	mA	

switching characteristics, V_{CC} = 5 V, T_A = 25°C

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{pd}	Propagation delay time, CLOCK to SERIAL OUT	C _L = 15 pF		0.2	0.5	μs
tDHL	Delay time, high-to-low-level Q output from STROBE or CLOCK inputs			0.2‡	0.6	μs
^t DLH	Delay time, low-to-high-level Q output from STROBE or CLOCK inputs	$C_L = 150 \text{ pF},$ $R_1 = 470 \Omega,$		0.35‡	1	μs
tTHL	Transition time, high-to-low-level Q output	See Figures 2 and 3		0.1	0.3	μs
tTLH	Transition time, low-to-high-level Q output			0.35	1	μs

[‡] Typical values are for clock Inputs. Typical values from STROBE will be less.



PARAMETER MEASUREMENT INFORMATION

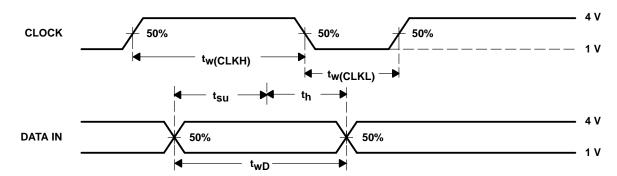


Figure 1. Input Timing Voltage Waveforms

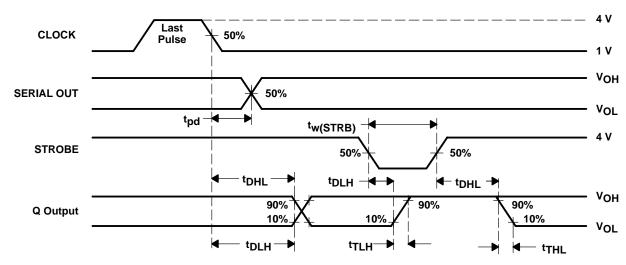
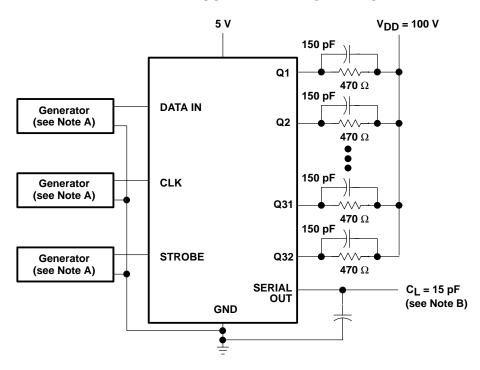


Figure 2. Switching Characteristics

PARAMETER MEASUREMENT INFORMATION



NOTES: A. Input pulses are supplied by generators having the following characteristics: t_W = 1.25 μ s, PRR \leq 200 kHz, $t_f \leq$ 30 ns, $t_f \leq$ 30 ns, Z_O = 50 Ω .

B. C_L includes probe and jig capacitance.

Figure 3. Test Circuit

LOW-LEVEL Q OUTPUT CURRENT

TYPICAL CHARACTERISTICS

LOW-LEVEL Q OUTPUT VOLTAGE FREE-AIR TEMPERATURE 10 $V_{CC} = 5 V$ 9 I_{OL} = 180 mA V_{OL} - Low-Level Output Voltage - V 8 7 6 5 4 3 2 0 0 10 70 20 30 40 50 60 80

Figure 4

T_A - Free-Air Temperature - °C

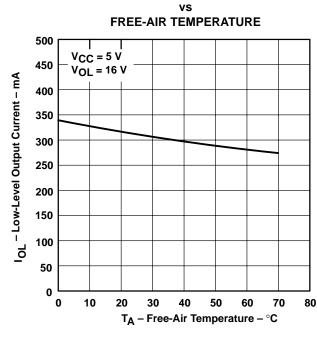
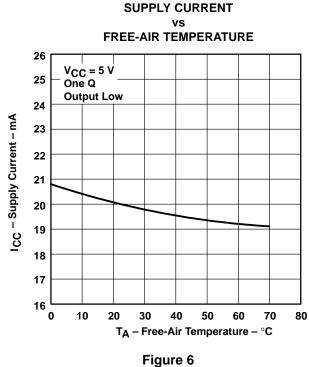


Figure 5

PROPAGATION DELAY TIME,



80

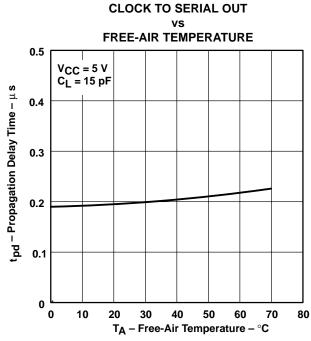


Figure 7

TYPICAL CHARACTERISTICS

DELAY TIME, HIGH-TO-LOW-LEVEL Q OUTPUT vs FREE-AIR TEMPERATURE

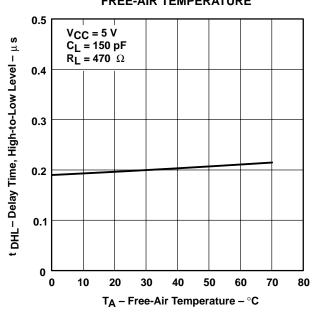


Figure 8

TRANSITION TIME, HIGH-TO-LOW-LEVEL vs

FREE-AIR TEMPERATURE

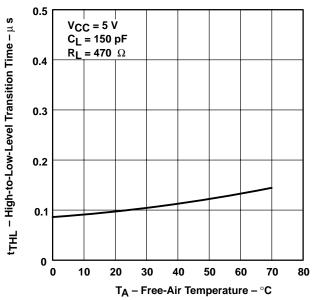


Figure 10

DELAY TIME, LOW-TO-HIGH-LEVEL Q OUTPUT vs

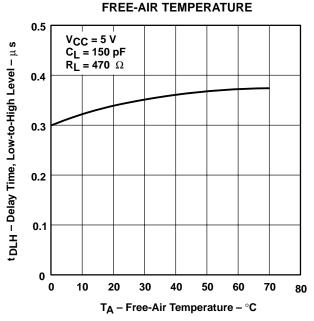


Figure 9

TRANSITION TIME, LOW-TO-HIGH-LEVEL Q OUTPUT

FREE-AIR TEMPERATURE

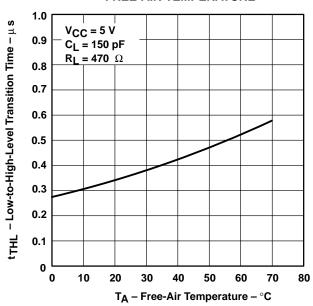


Figure 11



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